

NGTB30N120L2WG

IGBT - Field Stop II

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop II Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for motor driver applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

Features

- Extremely Efficient Trench with Field Stop Technology
- $T_{Jmax} = 175^{\circ}C$
- Soft Fast Reverse Recovery Diode
- Optimized for Low V_{CEsat}
- 10 μs Short Circuit Capability
- These are Pb-Free Devices

Typical Applications

- Motor Drive Inverter
- Industrial Switching
- Welding

ABSOLUTE MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|-----------|----------------------|-------------|
| Collector-emitter voltage | V_{CES} | 1200 | V |
| Collector current @ $T_c = 25^{\circ}C$ @ $T_c = 100^{\circ}C$ | I_c | 60 30 | A |
| Pulsed collector current, T_{pulse} limited by T_{Jmax} , 10 μs Pulse, $V_{GE} = 15 V$ | I_{CM} | 120 | A |
| Diode forward current @ $T_c = 25^{\circ}C$ @ $T_c = 100^{\circ}C$ | I_F | 60 30 | A |
| Diode pulsed current, T_{pulse} limited by T_{Jmax} | I_{FM} | 120 | A |
| Gate-emitter voltage Transient gate-emitter voltage ($T_{pulse} = 5 \mu s$, $D < 0.10$) | V_{GE} | ± 20 ± 30 | V |
| Power Dissipation @ $T_c = 25^{\circ}C$ @ $T_c = 100^{\circ}C$ | P_d | 534 267 | W |
| Short Circuit Withstand Time $V_{GE} = 15 V$, $V_{CE} = 500 V$, $T_J \leq 150^{\circ}C$ | T_{SC} | 10 | μs |
| Operating junction temperature range | T_J | -55 to +175 | $^{\circ}C$ |
| Storage temperature range | T_{stg} | -55 to +175 | $^{\circ}C$ |
| Lead temperature for soldering, 1/8" from case for 5 seconds | T_{SLD} | 260 | $^{\circ}C$ |

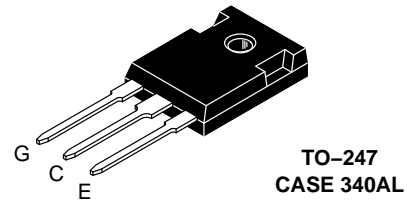
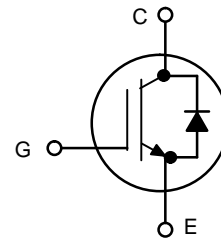
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



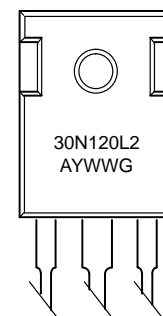
ON Semiconductor[®]

<http://onsemi.com>

30 A, 1200 V
 $V_{CEsat} = 1.70 V$
 $E_{off} = 1.4 mJ$



MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

| Device | Package | Shipping |
|----------------|------------------|-----------------|
| NGTB30N120L2WG | TO-247 (Pb-Free) | 30 Units / Rail |

NGTB30N120L2WG

THERMAL CHARACTERISTICS

| Rating | Symbol | Value | Unit |
|--|-----------------|-------|-----------------------------|
| Thermal resistance junction-to-case, for IGBT | $R_{\theta JC}$ | 0.28 | $^{\circ}\text{C}/\text{W}$ |
| Thermal resistance junction-to-case, for Diode | $R_{\theta JC}$ | 0.85 | $^{\circ}\text{C}/\text{W}$ |
| Thermal resistance junction-to-ambient | $R_{\theta JA}$ | 40 | $^{\circ}\text{C}/\text{W}$ |

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

| Parameter | Test Conditions | Symbol | Min | Typ | Max | Unit |
|-----------|-----------------|--------|-----|-----|-----|------|
|-----------|-----------------|--------|-----|-----|-----|------|

STATIC CHARACTERISTIC

| | | | | | | |
|---|---|---------------|------|--------------|-----------|----|
| Collector-emitter breakdown voltage, gate-emitter short-circuited | $V_{GE} = 0\text{ V}, I_C = 500\ \mu\text{A}$ | $V_{(BR)CES}$ | 1200 | – | – | V |
| Collector-emitter saturation voltage | $V_{GE} = 15\text{ V}, I_C = 30\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 30\text{ A}, T_J = 175^{\circ}\text{C}$ | V_{CEsat} | – | 1.70 2.07 | 1.90 – | V |
| Gate-emitter threshold voltage | $V_{GE} = V_{CE}, I_C = 400\ \mu\text{A}$ | $V_{GE(th)}$ | 4.5 | 5.5 | 6.5 | V |
| Collector-emitter cut-off current, gate-emitter short-circuited | $V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}$ $V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 175^{\circ}\text{C}$ | I_{CES} | – | – | 1.0 2 | mA |
| Gate leakage current, collector-emitter short-circuited | $V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$ | I_{GES} | – | – | 200 | nA |

| | | | | | | |
|------------------------------|--|-----------|---|------|---|----|
| Input capacitance | $V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$ | C_{ies} | – | 7500 | – | pF |
| Output capacitance | | C_{oes} | – | 200 | – | |
| Reverse transfer capacitance | | C_{res} | – | 140 | – | |
| Gate charge total | $V_{CE} = 600\text{ V}, I_C = 30\text{ A}, V_{GE} = 15\text{ V}$ | Q_g | – | 310 | – | nC |
| Gate to emitter charge | | Q_{ge} | – | 61 | – | |
| Gate to collector charge | | Q_{gc} | – | 150 | – | |

SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

| | | | | | | | |
|-------------------------|--|--------------|-------|-----|-----|----|----|
| Turn-on delay time | $T_J = 25^{\circ}\text{C}$ $V_{CC} = 600\text{ V}, I_C = 30\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$ | $t_{d(on)}$ | – | 116 | – | ns | |
| Rise time | | t_r | – | 35 | – | | |
| Turn-off delay time | | $t_{d(off)}$ | – | 285 | – | | |
| Fall time | | | t_f | – | 175 | – | mJ |
| Turn-on switching loss | | E_{on} | – | 4.4 | – | | |
| Turn-off switching loss | | E_{off} | – | 1.4 | – | | |
| Total switching loss | | E_{ts} | – | 5.8 | – | | |
| Turn-on delay time | $T_J = 175^{\circ}\text{C}$ $V_{CC} = 600\text{ V}, I_C = 30\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$ | $t_{d(on)}$ | – | 110 | – | ns | |
| Rise time | | t_r | – | 36 | – | | |
| Turn-off delay time | | $t_{d(off)}$ | – | 300 | – | | |
| Fall time | | | t_f | – | 331 | – | mJ |
| Turn-on switching loss | | E_{on} | – | 5.5 | – | | |
| Turn-off switching loss | | E_{off} | – | 2.5 | – | | |
| Total switching loss | | E_{ts} | – | 8.0 | – | | |

DIODE CHARACTERISTIC

| | | | | | | |
|--------------------------|---|-----------|---|--------------|-----------|---------------|
| Forward voltage | $V_{GE} = 0\text{ V}, I_F = 30\text{ A}$ $V_{GE} = 0\text{ V}, I_F = 30\text{ A}, T_J = 175^{\circ}\text{C}$ | V_F | – | 1.50 1.40 | 1.70 – | V |
| Reverse recovery time | $T_J = 25^{\circ}\text{C}$ $I_F = 30\text{ A}, V_R = 400\text{ V}$ $di_F/dt = 200\text{ A}/\mu\text{s}$ | t_{rr} | – | 450 | – | ns |
| Reverse recovery charge | | Q_{rr} | – | 7.85 | – | μC |
| Reverse recovery current | | I_{rrm} | – | 32 | – | A |

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TYPICAL CHARACTERISTICS

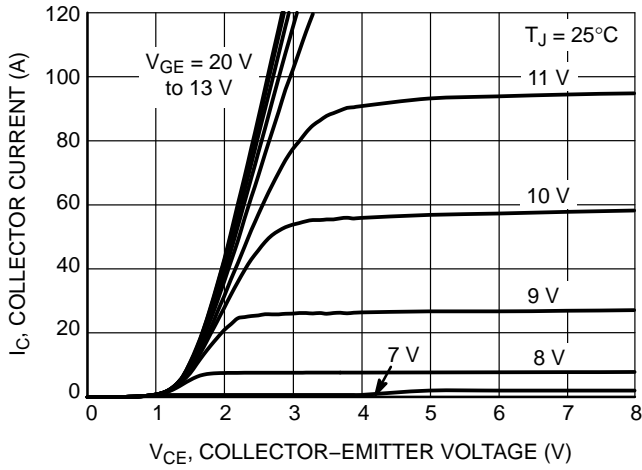


Figure 1. Output Characteristics

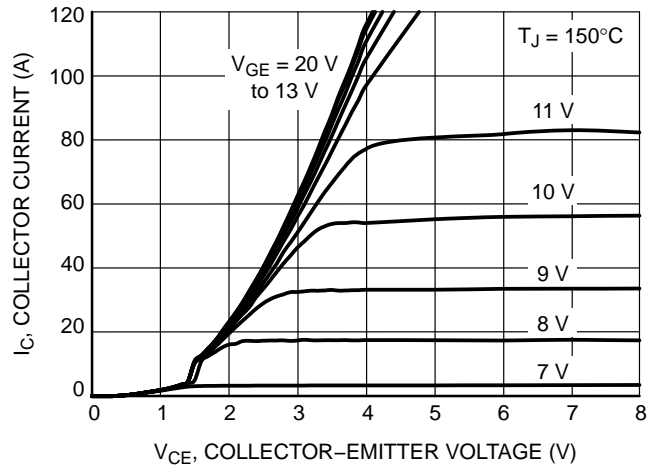


Figure 2. Output Characteristics

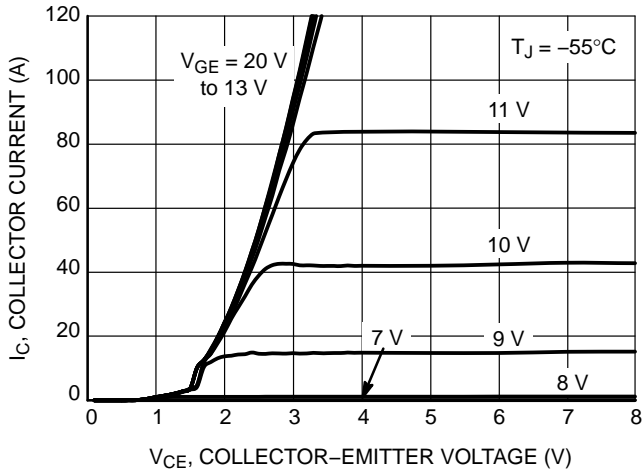


Figure 3. Output Characteristics

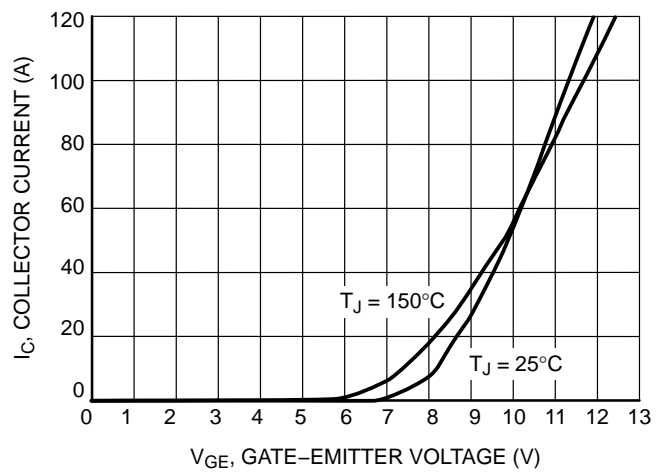


Figure 4. Typical Transfer Characteristics

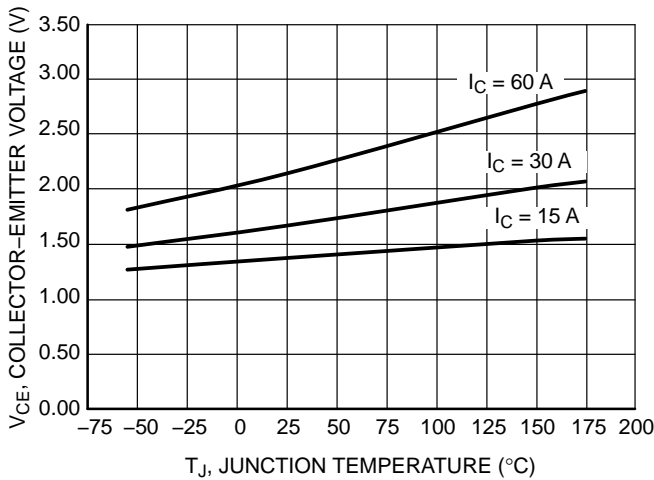


Figure 5. $V_{CE(sat)}$ vs T_J

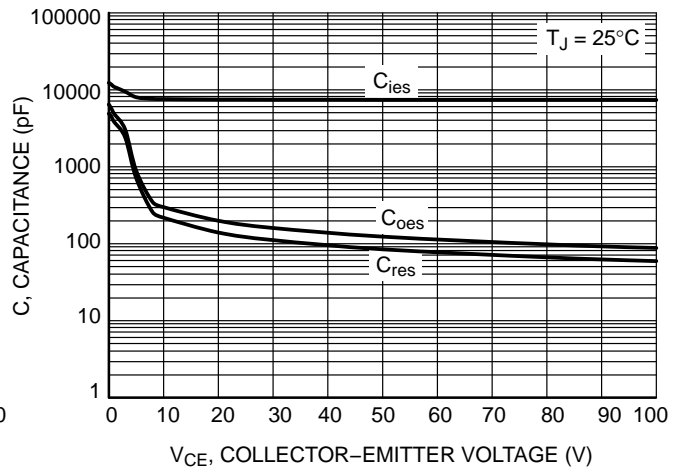


Figure 6. Typical Capacitance

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TYPICAL CHARACTERISTICS

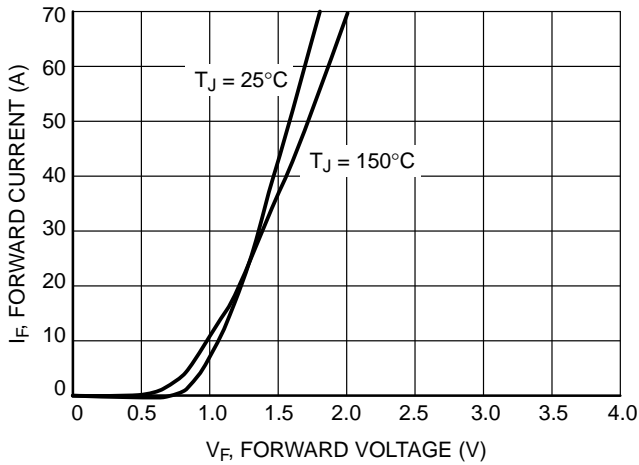


Figure 7. Diode Forward Characteristics

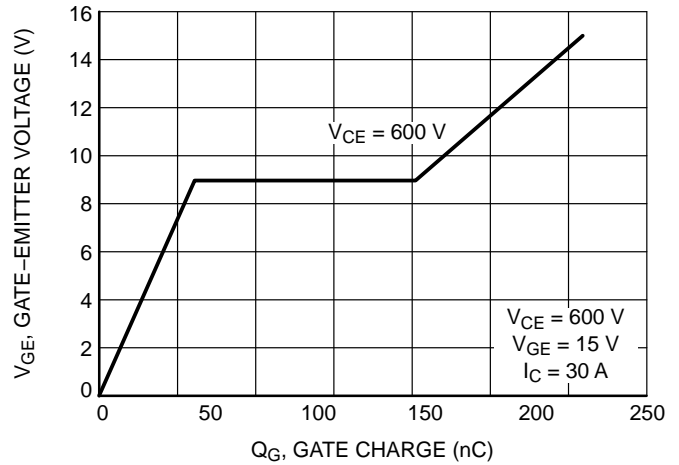


Figure 8. Typical Gate Charge

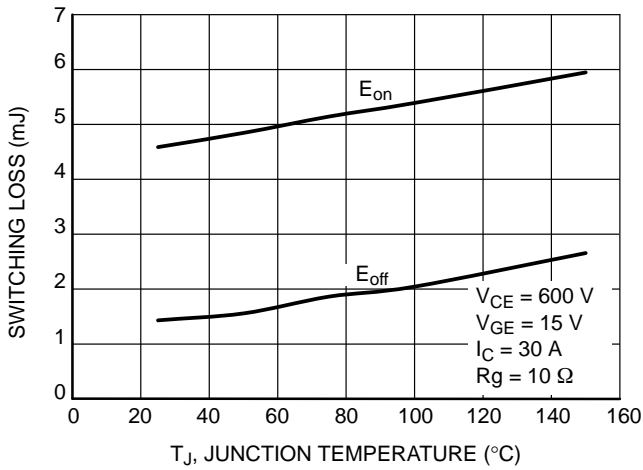


Figure 9. Switching Loss vs. Temperature

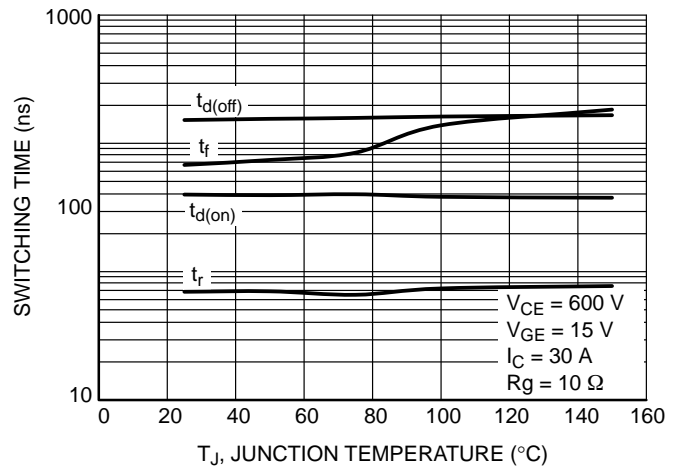


Figure 10. Switching Time vs. Temperature

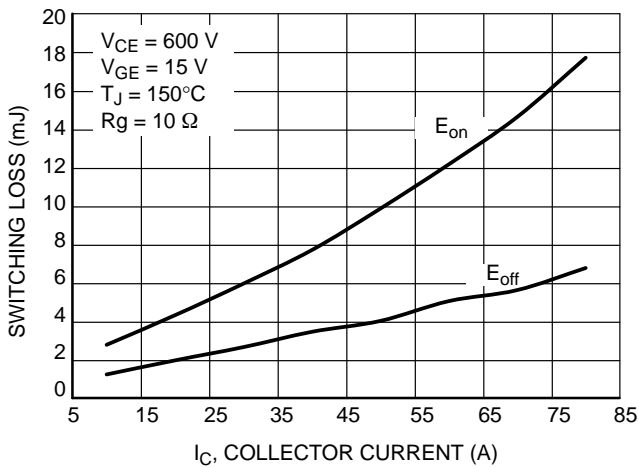


Figure 11. Switching Loss vs. I_C

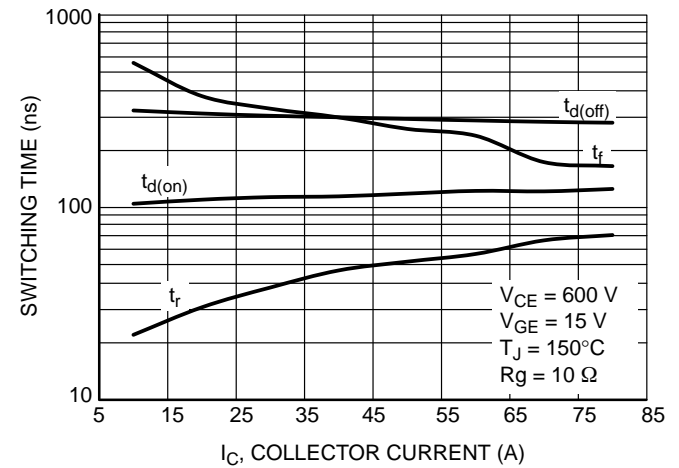


Figure 12. Switching Time vs. I_C

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TYPICAL CHARACTERISTICS

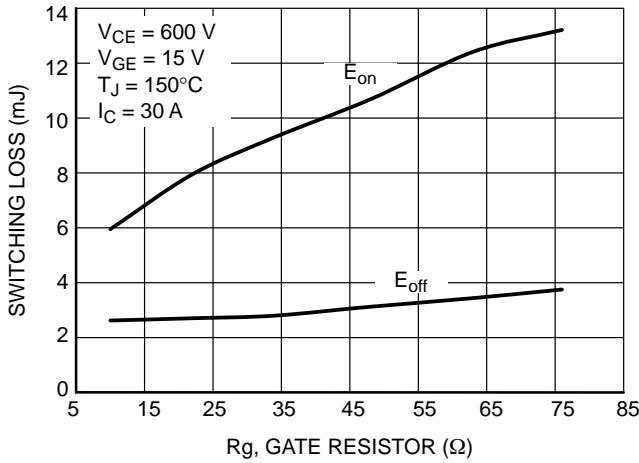


Figure 13. Switching Loss vs. R_g

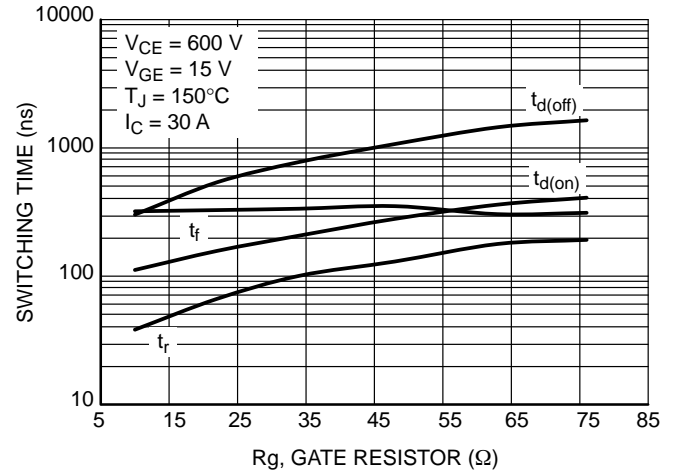


Figure 14. Switching Time vs. R_g

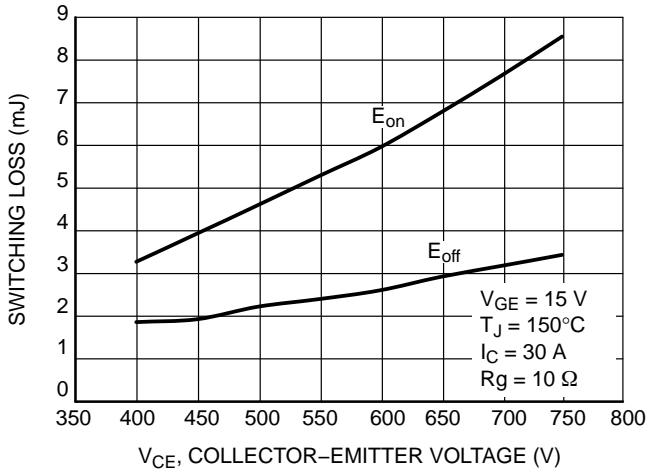


Figure 15. Switching Loss vs. V_{CE}

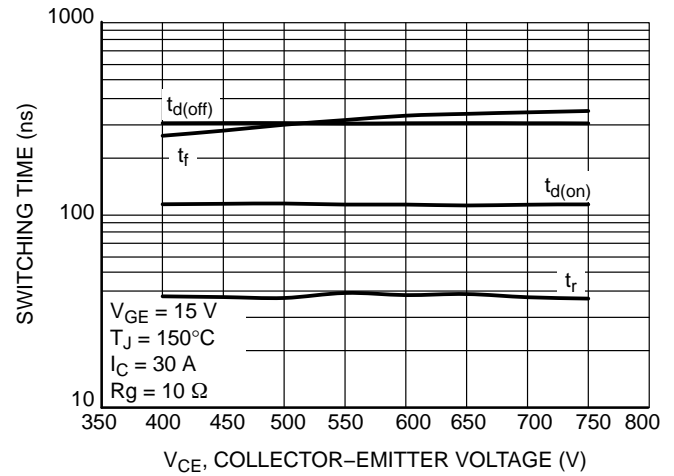


Figure 16. Switching Time vs. V_{CE}

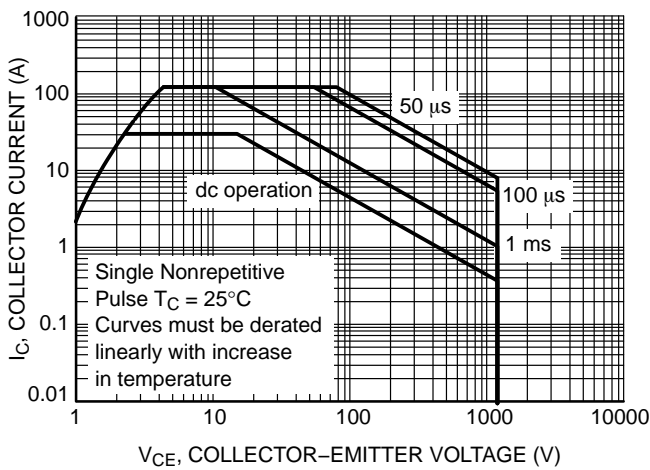


Figure 17. Safe Operating Area

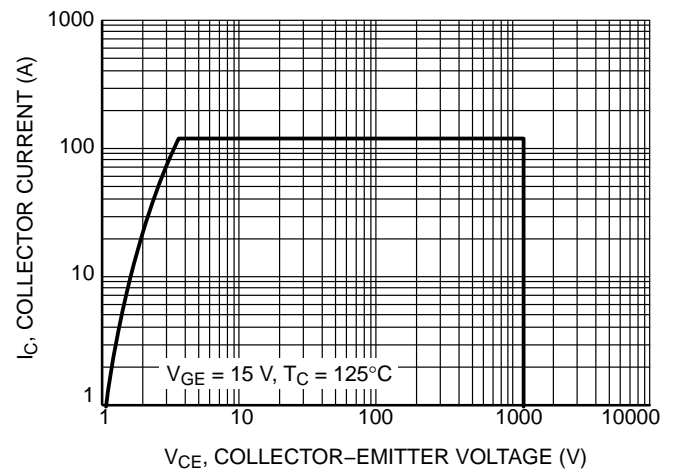


Figure 18. Reverse Bias Safe Operating Area

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TYPICAL CHARACTERISTICS

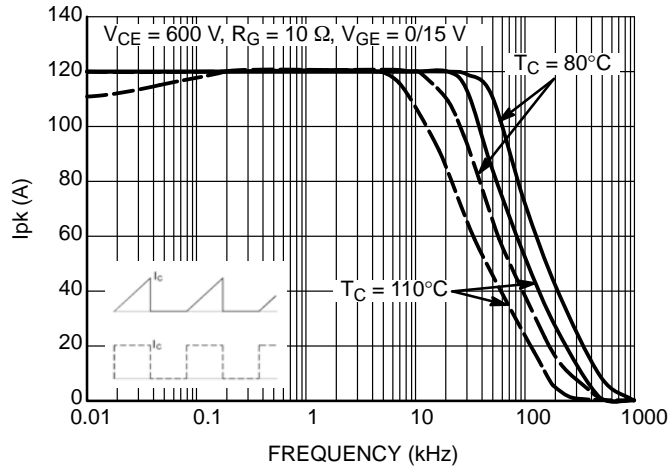


Figure 19. Collector Current vs. Switching Frequency

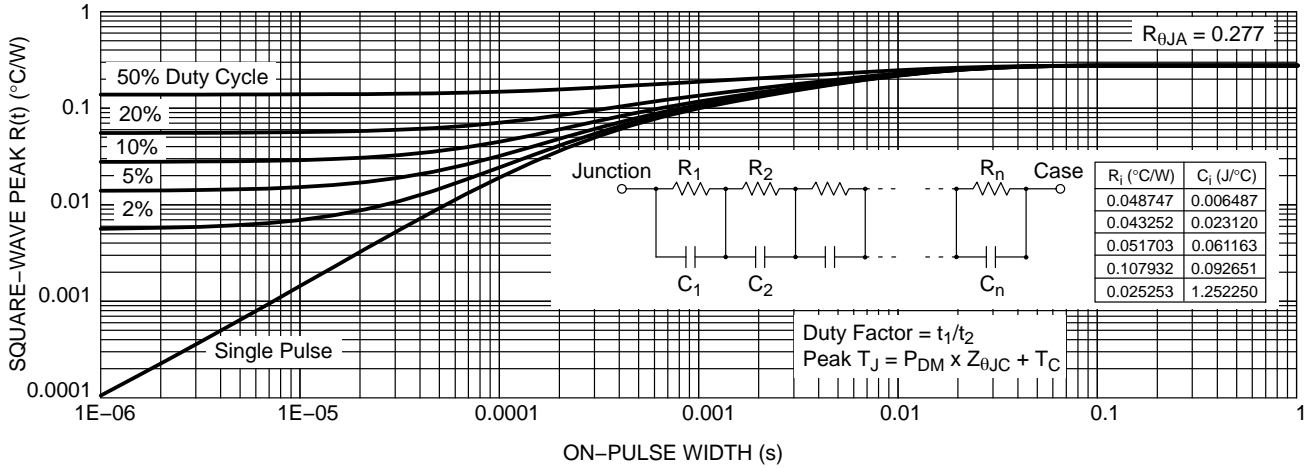


Figure 20. IGBT Transient Thermal Impedance

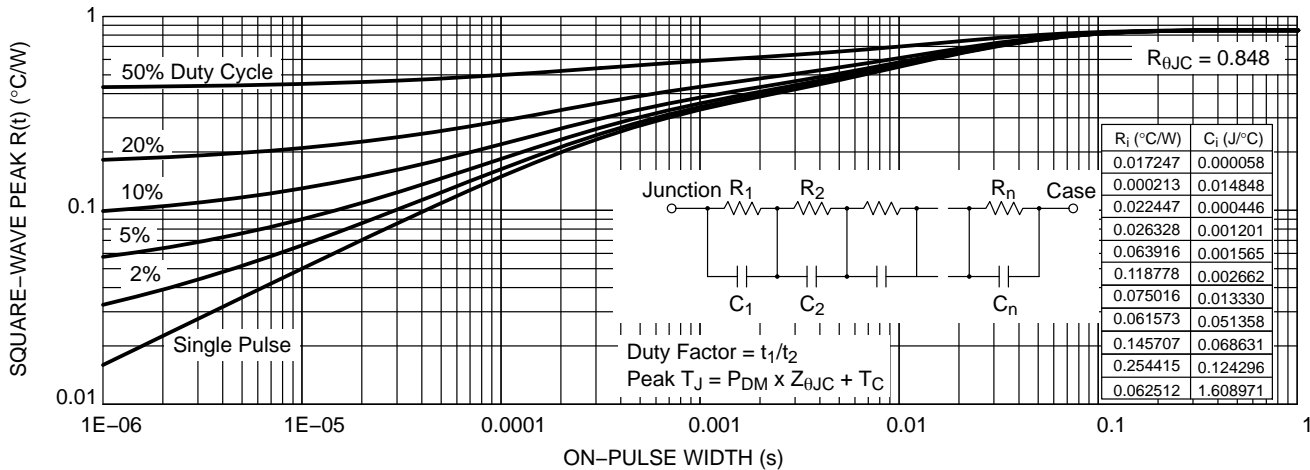
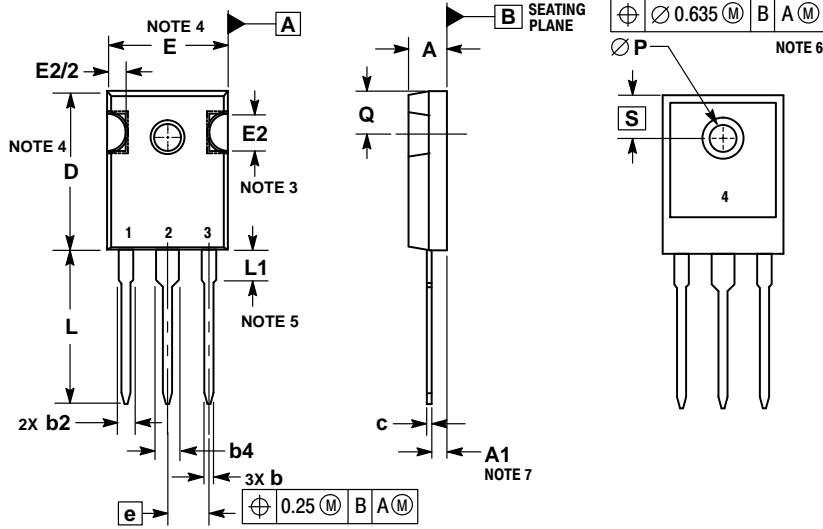


Figure 21. Diode Transient Thermal Impedance

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PACKAGE DIMENSIONS

TO-247 CASE 340AL ISSUE A



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
5. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.
6. $\varnothing\ P$ SHALL HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM DIAMETER OF 3.91.
7. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.

| MILLIMETERS | | |
|-------------|----------|-------|
| DIM | MIN | MAX |
| A | 4.70 | 5.30 |
| A1 | 2.20 | 2.60 |
| b | 1.00 | 1.40 |
| b2 | 1.65 | 2.35 |
| b4 | 2.60 | 3.40 |
| c | 0.40 | 0.80 |
| D | 20.30 | 21.40 |
| E | 15.50 | 16.25 |
| E2 | 4.32 | 5.49 |
| e | 5.45 BSC | |
| L | 19.80 | 20.80 |
| L1 | 3.50 | 4.50 |
| P | 3.55 | 3.65 |
| Q | 5.40 | 6.20 |
| S | 6.15 BSC | |

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